

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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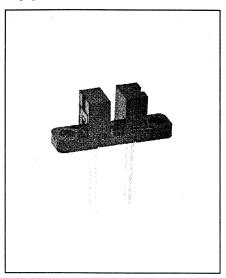


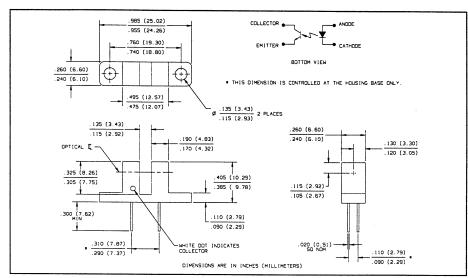






Slotted Optical Switches Types OPB845A, OPB845B





Features

- Non-contact switching
- Printed circuit board mounting
- 0.125" (3.18 mm) wide slot
- 0.300" (7.62 mm) lead spacing
- · Opaque plastic housing

Description

The OPB845 series consists of an infrared emitting diode and an NPN silicon phototransistor encased in an opaque housing on opposite sides of a .125" (3.18 mm) wide slot. The opaque housing, with molded apertures, provides protection in areas where ambient radiation may be a concern. The "A" option offers a .050" (1.27 mm) wide aperture molded in front of the phototransistor while the "B" version offers a .010" (0.254 mm) wide aperture.

Phototransistor

OPB# Aperture Width

OPB845A 0.050" OPB845B 0.010"

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage and Operating Temperature Range40° C to +85° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering
iron]
Input Diode
Forward DC Current 50 mA
Peak Forward Current (1µs pulse width, 300 pps)
Reverse DC Voltage 2.0 V
Power Dissipation
Output Phototransistor
Collector-Emitter Voltage
Emitter-Collector Voltage
Collector DC Current
Power Dissipation
Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 sec. max. when flow soldering.
- (2) Derate Linearly 1.67 mW/° C above 25° C.
- (3) All parameters tested using pulse technique.
- (4) Methanol or isopropanol are recommended as cleaning agents. Plastic housing is soluble in chlorinated hydrocarbons and ketones.



Carrollton, Texas 75006

Types OPB845A, OPB845B

Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS	TEST CONDITIONS
Input Diod	e				
VF	Forward Voltage		1.7	V	I _F = 20 mA
IR	Reverse Current		100	μА	V _R = 2 V
Output Pho	ototransistor			.,	
V _(BR) CEO	Collector-Emitter Breakdown Voltage	30		V	Ic = 1 mA
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0		V	ΙΕ = 100 μΑ
ICEO	Collector-Emitter Dark Current		100	nA	$V_{CE} = 10V$, $I_F = 0$, $E_e = 0$
Coupled					
VCE(SAT)	Saturation Voltage		0.6	V	I _C = 1800 μA, I _F = 20 mA
Ic(ON)	On-State Collector Current	1800		μА	V _{CE} = 0.6 V, I _F = 20 mA

